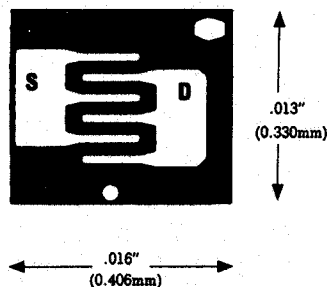


CHIP NUMBER

FP22.2



Die Size: 13 x 16 (mils)  
0.330 x 0.406(mm)  
4 x 6 (mils)  
Pad Size: 0.102 x 0.152(mm)  
GATE-SUBSTRATE

#### CONTACT METALLIZATION

Top Contact: > 12,000  
Å Aluminum

Backside Contact: 3,000 Å Gold

#### ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

## TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
$B_{VGSS}$	40	55		V	$V_{DS} = 0, I_G = 1\mu A$
$I_{DSS}$	0.1		6	mA	$V_{DS} = -15V, V_{GS} = 0$
$V_p$	0.5		6	V	$V_{DS} = -15V, I_D = 1nA$
$I_{GSS}$		20	100	pA	$V_{DS} = 0, V_{GS} = 30V$
$G_m$	0.2	1	2	mS	$V_{DS} = -15V, V_{GS} = 0, f = 1KHz$
$C_{iss}$		4	5	pF	$V_{DS} = -15, V_{GS} = 0, f = 1MHz$
$C_{rss}$		0.9	1.5	pF	$V_{DS} = -15V, V_{GS} = 0, f = 1MHz$

TYPICAL DEVICE TYPES: 2N2606 - 2N2608, 2N3376, 2N3378, 2N3695 - 2N3698

CHIP TYPE FP22.2

